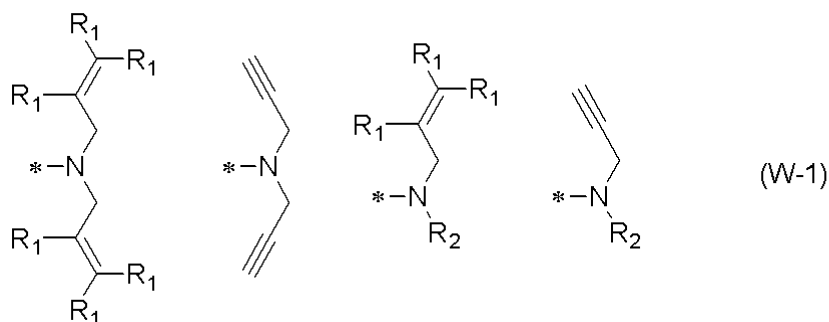


TITLE OF INVENTION: COMPOUND FOR FORMING METAL-CONTAINING
FILM, COMPOSITION FOR FORMING METAL-CONTAINING FILM, AND
PATTERNING PROCESS

ABSTRACT

The present invention is a compound for forming a metal-containing film to be contained in a composition for forming a metal-containing film, where the compound is a metal compound including at least one kind of metal atom selected from the group consisting of Ti, Zr, and Hf and a ligand coordinated to the metal atom, and the ligand includes a crosslinking group represented by one of the following general formulae (W-1). This provides: a compound for forming a metal-containing film having better dry etching resistance than conventional resist underlayer film materials and also having high filling and planarizing properties; a composition for forming a metal-containing film containing the compound; and a patterning process in which the composition is used.



[Fig.1]